MSKSEMI















ESD

TVS

TSS

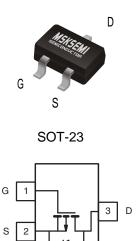
MOV

GDT

PLED

Broduct data sheet





Features

- -30V, -3.4A, $RDS(ON) = 75m\Omega@VGS = -10V$
- Fast switching
- Green Device Available
- Suit for -4.5V Gate Drive Applications

Applications

- Notebook
- Load Switch
- Battery Protection
- Hand-held Instruments

BVDSS	RDSON	ID
-30V	75m Ω	-3.4A

Absolute Maximum Ratings Tc=25°C unless otherwise noted

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	-30	V
V _G s	Gate-Source Voltage	±20	V
	Drain Current – Continuous (T _A =25°C)	-3.4	Α
ID	Drain Current – Continuous (T _A =70°C)	-2.64	А
I _{DM}	Drain Current – Pulsed ¹	-13.2	Α
D-	Power Dissipation (T _A =25°C)	1.56	W
P _D	Power Dissipation – Derate above 25°C	0.012	W/°C
T _{STG}	Storage Temperature Range	-55 to 150	°C
TJ	Operating Junction Temperature Range	-55 to 150	°C

Thermal Characteristics

Symbol	Parameter	Тур.	Max.	Unit
RθJA	Thermal Resistance Junction to ambient		80	°C/W



Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Off Characteristics

Symbol	Parameter Conditions		Min.	Тур.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =-250uA	- 30			V
△BV _{DSS} /△T _J	BV _{DSS} Temperature Coefficient Reference to 25°C , I _D =-1mA			- 0.02		V/°C
	Dunin Course Lookens Courset	V _{DS} =-27V , V _{GS} =0V , T _J =25°C			-1	uA
I _{DSS} Drain-Source Leakage Current	V _{DS} =-24V , V _{GS} =0V , T _J =125°C			-10	uA	
Igss	Gate-Source Leakage Current	V _{GS} =±20V , V _{DS} =0V			±100	nA

On Characteristics

Proven	Static Drain-Source On-Resistance	V _{GS} =-10V , I _D =-3A		75	95	mΩ
R _{DS(ON)} Static Drain-Source On-Resistance		V _{GS} =-4.5V , I _D =-2A		110	145	mΩ
V _{GS(th)}	Gate Threshold Voltage	\\ \\ \\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	- 1.0	- 1.6	- 2.5	V
$\triangle V_{GS(th)}$	V _{GS(th)} Temperature Coefficient	$V_{GS}=V_{DS}$, $I_D=-250uA$		-2.8		mV/°C
gfs	Forward Transconductance	V _{DS} =-10V , I _D =-1A		3		S

Dynamic and switching Characteristics

	_					
Qg	Total Gate Charge ^{2, 3}			2.5		
Q_{gs}	Gate-Source Charge ^{2, 3}	V _{DS} =-24V , V _{GS} =-4.5V , I _D =-2A		0.1		nC
Q_{gd}	Gate-Drain Charge ^{2,3}			1.8	-	
T _{d(on)}	Turn-On Delay Time ^{2, 3}			6.1	-	
Tr	Rise Time ^{2,3}	V_{DD} =-15V , V_{GS} =-10V , R_{G} =6 Ω		8.7	-	no
T _{d(off)}	Turn-Off Delay Time ^{2, 3}	I _D =-1A		33.2	-	ns
Tf	Fall Time ^{2, 3}			3.7		
C _{iss}	Input Capacitance			226		
Coss	Output Capacitance	V _{DS} =-15V , V _{GS} =0V , F=1MHz		39		pF
Crss	Reverse Transfer Capacitance			29		
Rg	Gate resistance	V _{GS} =0V, V _{DS} =0V, F=1MHz		9.5		Ω

Drain-Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Is	Continuous Source Current	V _G =V _D =0V . Force Current			- 3.3	Α
I _{SM}	Pulsed Source Current	VG-VD-UV , Force Current			- 6.6	Α
V _{SD}	Diode Forward Voltage	V _{GS} =0V , I _S =-1A , T _J =25°C			- 1.2	V

tive Rating: Pulsed width limited by maximum junction temperature.

 $[\]begin{array}{ll} 2. & \text{ The data tested by pulsed , pulse width } \leqq 300 us \text{ , duty cycle} \leqq 2\%. \\ 3. & \text{ Essentially independent of operating temperature.} \end{array}$



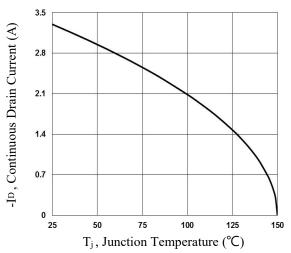


Fig.1 Continuous Drain Current vs. Tc

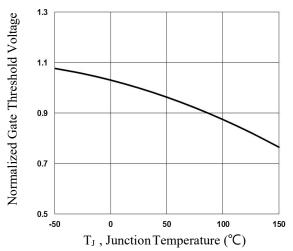


Fig.3 Normalized V_{th} vs. T_J

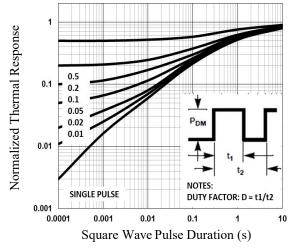


Fig.5 Normalized Transient Impedance

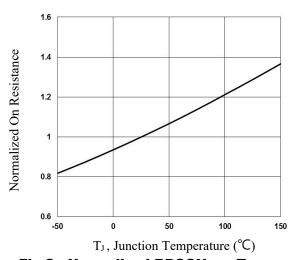


Fig.2 Normalized RDSON vs. T_J

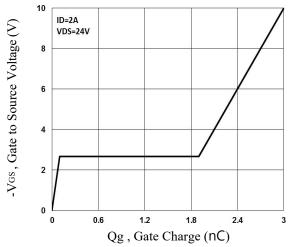


Fig.4 Gate Charge Waveform

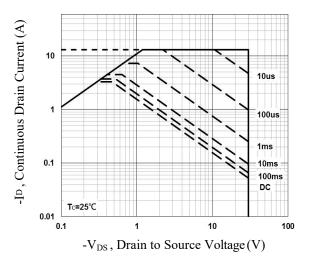
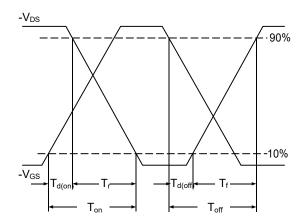


Fig.6 Maximum Safe Operation Area





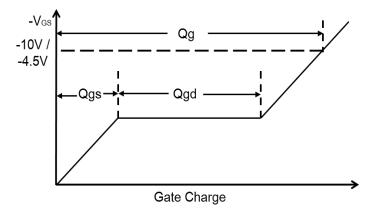
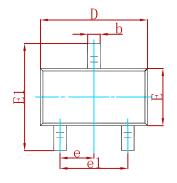


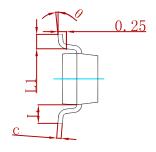
Fig.7 Switching Time Waveform

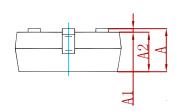
Fig.8 Gate Charge Waveform



PACKAGE MECHANICAL DATA

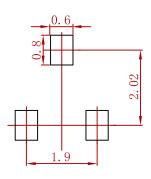






Symbol	Dimensions	Dimensions In Millimeters		s In Inches
Symbol	Min	Max	Min	Max
Α	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
С	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
Е	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
е	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550	0.550 REF 0.022 REF		2 REF
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

Suggested Pad Layout



- 1.Controlling dimension:in millimeters.2.General tolerance:± 0.05mm.3.The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
SI2307CDS	SOT-23	3000



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